

HIGH DENSITY MOUNTING AC INPUT, PHOTOTRANSISTOR OPTICALLY COUPLED ISOLATORS

DESCRIPTION

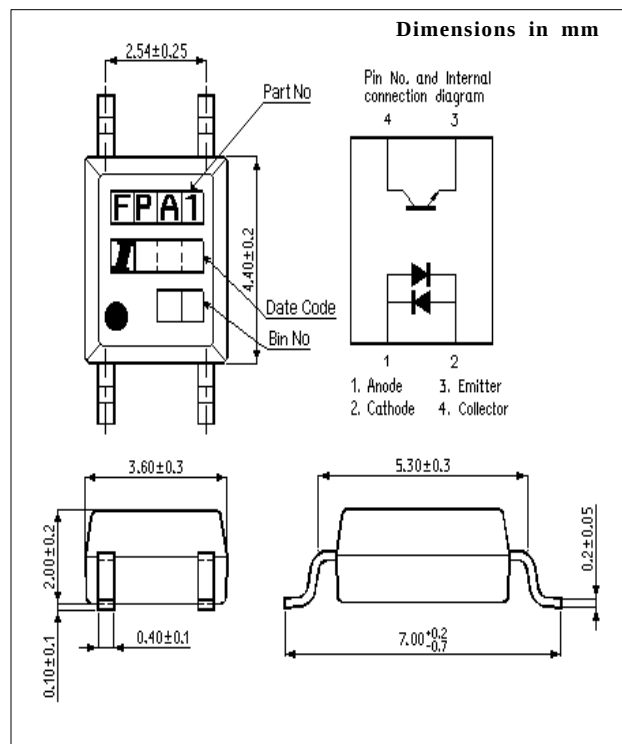
The IS354 is an optically coupled isolator consisting of two infrared light emitting diodes connected in inverse parallel and NPN silicon photo transistor in a space efficient dual in line plastic package.

FEATURES

- Marked as FPA1.
- Current Transfer Ratio MIN. 20%
- Isolation Voltage ($3.75kV_{RMS}$, $5.3kV_{PK}$)
- All electrical parameters 100% tested
- Drop in replacement for Sharp PC354

APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances



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ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature _____ -40°C to + 125°C
Operating Temperature _____ -30°C to + 100°C
Lead Soldering Temperature
(1/16 inch (1.6mm) from case for 10 secs) 260°C

INPUT DIODE

Forward Current _____ ±50mA
Reverse Voltage _____ 6V
Power Dissipation _____ 70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO} _____ 35V
Emitter-collector Voltage BV_{ECO} _____ 6V
Power Dissipation _____ 150mW

POWER DISSIPATION

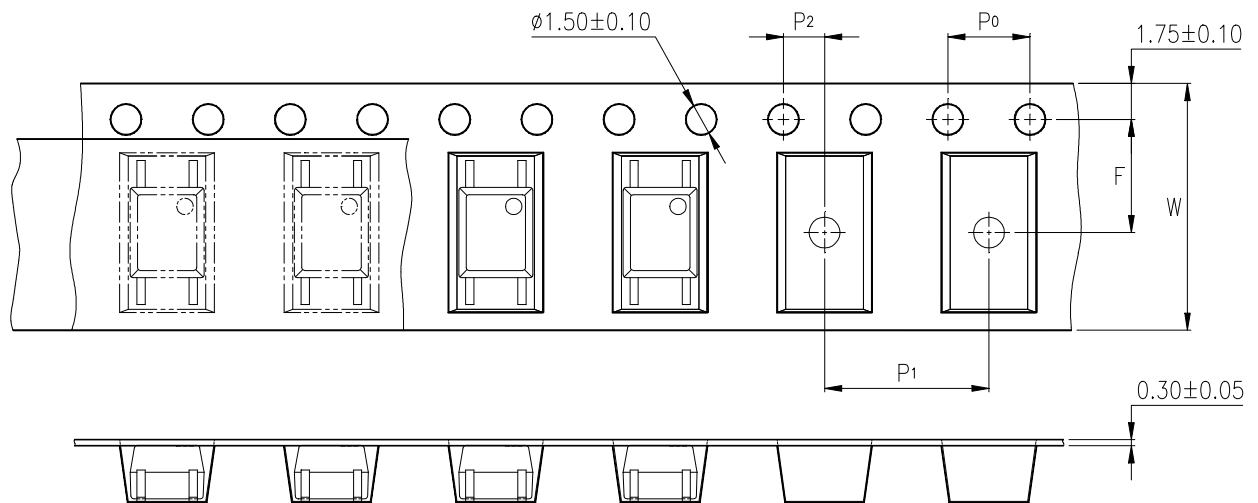
Total Power Dissipation _____ 170mW
(derate linearly 2.26mW/°C above 25°C)

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)	5	1.2	1.4	V	$I_F = \pm 20\text{mA}$ $I_R = 10\mu\text{A}$ $V_R = 4\text{V}$
	Reverse Voltage (V_R)			10	V	
	Reverse Current (I_R)				μA	
Output	Collector-emitter Breakdown (BV_{CEO})	35		100	V	$I_C = 0.1\text{mA}$
	Emitter-collector Breakdown (BV_{ECO})	6			V	$I_E = 10\mu\text{A}$ $V_{CE} = 20\text{V}$
	Collector-emitter Dark Current (I_{CEO})				nA	
Coupled	Current Transfer Ratio (CTR)	20		400	%	$\pm 1\text{mA } I_F, 5\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.2	V	$\pm 20\text{mA } I_F, 1\text{mA } I_C$
	Input to Output Isolation Voltage V_{ISO}	3750 5300			V_{RMS} V_{PK}	See note 1 See note 1
	Input-output Isolation Resistance R_{ISO}	5×10^{10}			Ω	$V_{IO} = 500\text{V}$ (note 1)
	Output Rise Time t_r		4	18	μs	$V_{CE} = 2\text{V},$ $I_C = 2\text{mA}, R_L = 100\Omega$
	Output Fall Time t_f		3	18	μs	

Note 1 Measured with input leads shorted together and output leads shorted together.

TAPING DIMENSIONS



Description	Symbol	Dimensions in mm (inches)
Tape wide	W	12 ± 0.3 (.47)
Pitch of sprocket holes	P ₀	4 ± 0.1 (.15)
Distance of compartment	F	5.5 ± 0.1 (.217)
Distance of compartment to compartment	P ₁	8 ± 0.1 (.315)
	P ₂	2 ± 0.1 (.079)

CHARACTERISTIC CURVES

Fig.1 Forward Current vs. Ambient Temperature

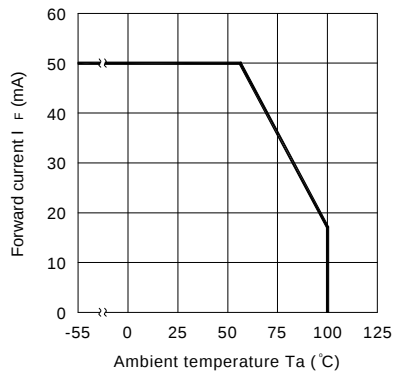


Fig.2 Collector Power Dissipation vs. Ambient Temperature

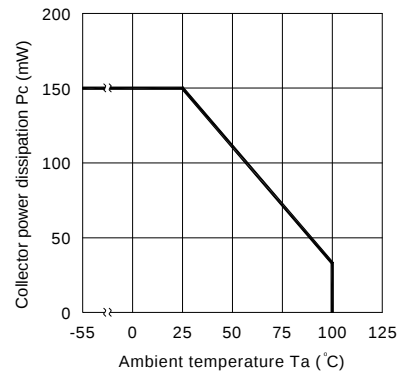


Fig.3 Collector-emitter Saturation Voltage vs. Forward Current

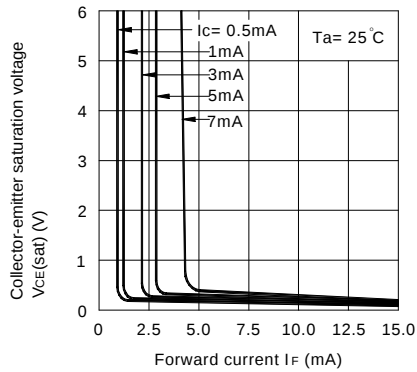


Fig.4 Forward Current vs. Forward Voltage

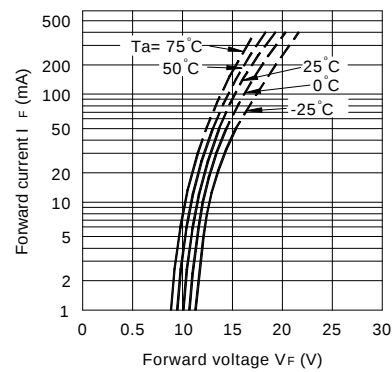


Fig.5 Current Transfer Ratio vs. Forward Current

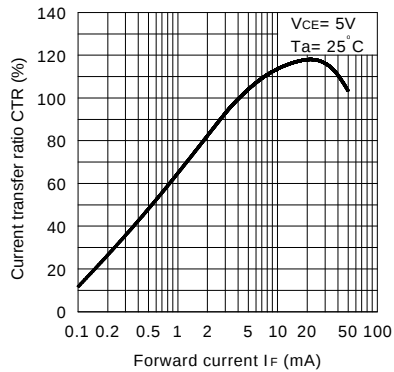
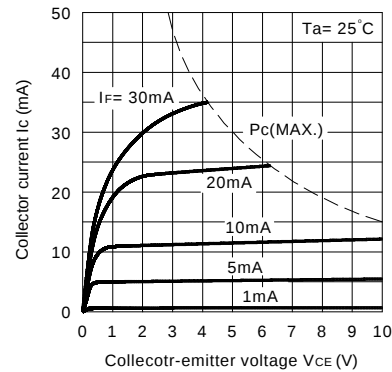


Fig.6 Collector Current vs. Collector-emitter Voltage



CHARACTERISTIC CURVES

Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

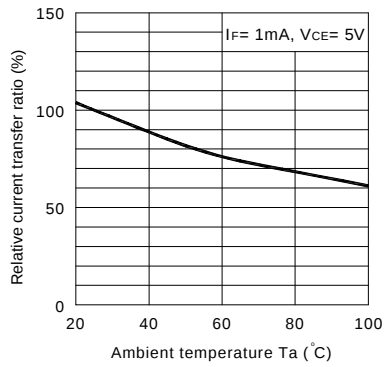


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

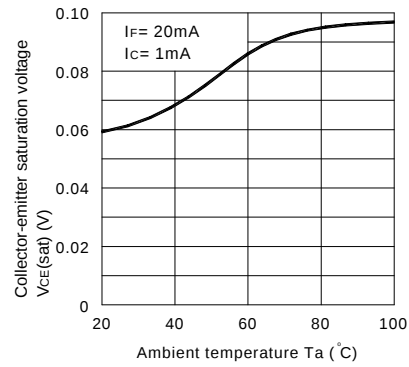


Fig.9 Collector Dark Current vs. Ambient Temperature

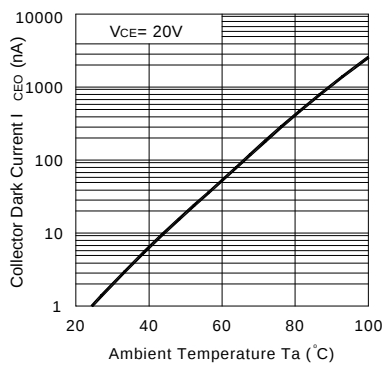


Fig.10 Response Time vs. Load Resistance

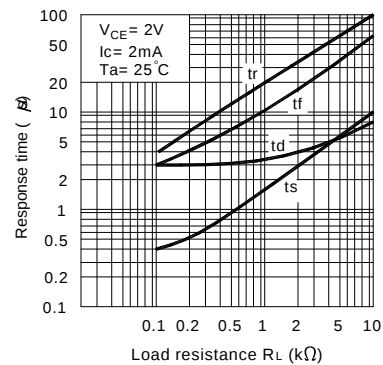
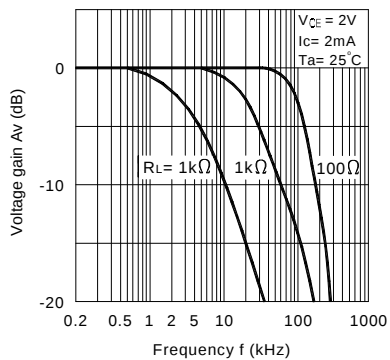
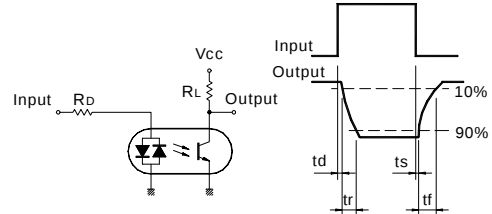


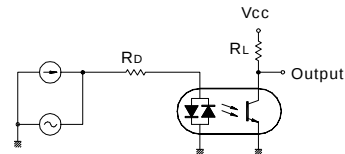
Fig.11 Frequency Response



Test Circuit for Response Time

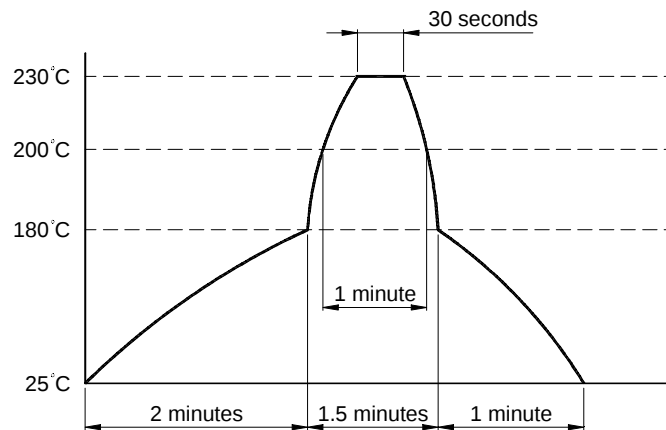


Test Circuit for Frequency Response



TEMPERATURE PROFILE OF SOLDERING REFLOW

- (1) One time soldering reflow is recommended within the condition of temperature and time profile shown below.



- (2) When using another soldering method such as infrared ray lamp, the temperature may rise partially in the mold of the device.
Keep the temperature on the package of the device within the condition of above (1).